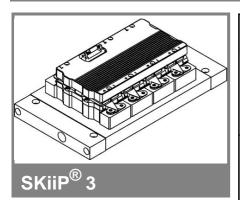
## **SKiiP 2403GB122-4DW**



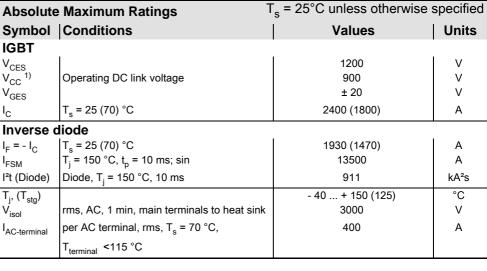
# 2-pack-integrated intelligent Power System

### Power section SKiiP 2403GB122-4DW

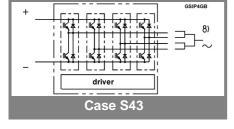
**Preliminary Data** 

#### **Features**

- SKiiP technology inside
- SPT (Soft Punch Trough) IGBTs
- CAL diode technology
- · Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP<sup>®</sup> 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized File no. E63532
- with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- AC connection busbars must be connected by the user; copper busbars available on request

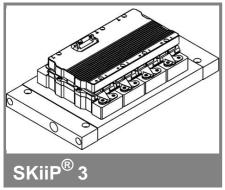


					T - 059	°C	- 4l m;	ifi-d
Characteristics				T <sub>s</sub> = 25°C unless otherwise specified				
_	Conditions			min.	typ.	max.	Units	
IGBT	ř.							Ī
V <sub>CEsat</sub>	I <sub>C</sub> = 1200 A measured at te	x, T <sub>j</sub> = 25 rminal	(125) °C;			2,3 (2,5)	2,6	V
$V_{CEO}$	T <sub>i</sub> = 25 (125) °C; at terminal				1,1 (1)	1,3 (1,2)	V	
$r_{CE}$	T <sub>i</sub> = 25 (125) °C; at terminal					1 (1,2)	1,1 (1,4)	mΩ
I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = V <sub>CES</sub> , T <sub>i</sub> = 25 (125) °C					mA		
$E_{on} + E_{off}$	$I_{\rm C} = 1200  \text{A}$	$V_{CC} = 6$	00 V		360			mJ
	T <sub>j</sub> = 125 °C	, V <sub>CC</sub> = 9	00 V		635			mJ
R <sub>CC+EE</sub>	terminal chi	ip, T <sub>i</sub> = 25	5 °C		0,13			mΩ
L <sub>CE</sub>	top, bottom					3		nΗ
C <sub>CHC</sub>	per phase,	per phase, AC-side			4			nF
Inverse o	diode							
$V_F = V_{EC}$	I <sub>F</sub> = 1200 A measured at te		(125) °C			1,95 (1,7)	2,1	V
$V_{TO}$	T <sub>i</sub> = 25 (125	5) °C				1,1 (0,8)	1,2 (0,9)	V
r <sub>T</sub>	$T_i = 25 (125)$	, 5) °C				0,7 (0,8)	0,8 (0,9)	mΩ
E <sub>rr</sub>	I <sub>C</sub> = 1200 A	$V_{CC} = 6$	00 V		96			mJ
	T <sub>i</sub> = 125 °C, V <sub>CC</sub> = 900 V				122			mJ
Mechani	cal data							
M <sub>dc</sub>	DC termina	ls, SI Uni	its		6		8	Nm
$M_{ac}$	AC termina	'			13		15	Nm
W	SKiiP® 3 System w/o heat sink				3,1		kg	
W	heat sink					97		kg
						:ol); "s" re	eference t	o heat
	reference	to bui	lt-in tem	perature	sensor			1
$R_{th(j-s)l}$	per IGBT						0,013	K/W
$R_{th(j-s)D}$	per diode						0,025	K/W
$Z_{th}$	R <sub>i</sub> (mK/W) (max. values)			tau <sub>i</sub> (s)				
	1	2	3	4	1	2	3	4
Z <sub>th(j-r)I</sub>	1,2	5 3	5,8	0 12.5	69 50	0,35 5	0,02	1
Z <sub>th(j-r)D</sub>	2		13,5	13,5	50		0,25	0,04
$Z_{th(r-a)}$	2,7	4,6	1,1	0,6	48	15	2,8	0,4



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## **SKiiP 2403GB122-4DW**



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2-pack-i	ntegrated
intelliger	nt Power System

2-pack integrated gate driver SKiiP 2403GB122-4DW

**Preliminary Data** 

#### **Gate driver features**

- · CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and

DC-bus voltage (option)

- Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute	Maximum Ratings	T <sub>a</sub> = 25°C unless otherwise specified		
Symbol	Conditions	Values	Units	
$V_{S2}$	unstabilized 24 V power supply	30	V	
$V_{i}$	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
$V_{isollO}$	input / output (AC, rms, 2s)	3000	V	
V <sub>isoIPD</sub>	partial discharge extinction voltage, rms, Q <sub>PD</sub> ≤10 pC;	1170	V	
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, 2s)	1500	V	
f <sub>sw</sub>	switching frequency	8	kHz	
f <sub>out</sub>	output frequency for I=I <sub>C</sub> ; sin.	1	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

Characte	eristics	(T <sub>a</sub> = 25°C			
Symbol	Conditions	min.	typ.	max.	Units
$V_{S2}$	supply voltage non stabilized	13	24	30	V
I <sub>S2</sub>	V <sub>S2</sub> = 24 V	324+39*f/kHz+0,00011*(I <sub>AC</sub> /A) <sup>2</sup>			mA
V <sub>iT+</sub>	input threshold voltage (High)	12,3		12,3	V
$V_{iT-}$	input threshold voltage (Low)	4,6			V
R <sub>IN</sub>	input resistance		10		kΩ
C <sub>IN</sub>	input capacitance		1		nF
t <sub>d(on)IO</sub>	input-output turn-on propagation time		1,3		μs
t <sub>d(off)IO</sub>	input-output turn-off propagation time		1,3		μs
t <sub>pERRRESET</sub>	error memory reset time		9		μs
$t_{TD}$	top / bottom switch interlock time		3,3		μs
I <sub>analogOUT</sub>	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		2000		Α
I <sub>s1out</sub>	max. load current			50	mA
I <sub>TRIPSC</sub>	over current trip level (I <sub>analog</sub> OUT = 10 V)	440	2500	100	A
T <sub>tp</sub>	over temperature protection	110	not	120	°C V
U <sub>DCTRIP</sub>	U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9 V);	i	not implemente	d	V
	(option for GB types)				

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